



# 2N70Z

*Power MOSFET*

## 2A, 700V N-CHANNEL POWER MOSFET

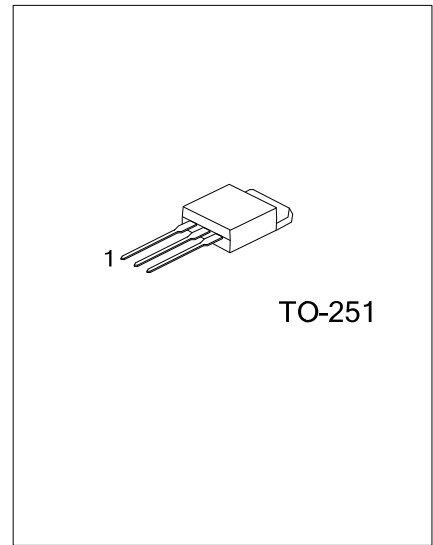
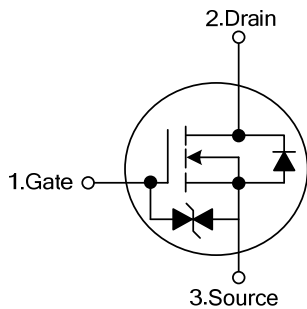
### DESCRIPTION

The UTC **2N70Z** is a high voltage MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in the high speed switching applications of power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

### FEATURES

- \*  $R_{DS(ON)} = 6.3\Omega @ V_{GS} = 10V$
- \* Ultra Low gate charge (typical 8.1nC)
- \* Low reverse transfer capacitance ( $C_{RSS} =$  typical 5.0 pF)
- \* Fast switching capability
- \* Avalanche energy specified
- \* Improved dv/dt capability, high ruggedness

### SYMBOL



### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N70ZL-TM3-T	2N70ZG-TM3-T	TO-251	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>2N70ZL-TA3-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Lead Plating</p>	<p>(1) T: Tube</p> <p>(2) TM3: TO-251</p> <p>(3) L: Lead Free, G: Halogen Free</p>
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■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DSS}$	700	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Avalanche Current (Note 2)	$I_{AR}$	2.0	A
Drain Current	Continuous	$I_D$	2.0
	Pulsed (Note 2)	$I_{DM}$	8.0
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	140
	Repetitive (Note 2)	$E_{AR}$	2.8
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Power Dissipation	$P_D$	30	W
Junction Temperature	$T_J$	+150	$^\circ\text{C}$
Operating Temperature	$T_{OPR}$	-55 ~ +150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by  $T_J$

3.  $L=45\text{mH}$ ,  $I_{AS}=2.0\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD}\leq 2.0\text{A}$ ,  $di/dt\leq 200\text{A}/\mu\text{s}$ ,  $V_{DD}\leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	110	$^\circ\text{C}/\text{W}$
Junction to Case	$\theta_{Jc}$	4.24	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ( $T_J=25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0\text{V}$ , $I_D = 250\ \mu\text{A}$	700			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 700\text{V}$ , $V_{GS} = 0\text{V}$			10	$\mu\text{A}$
Gate-Source Leakage Current	Forward Reverse	$I_{GSS}$	$V_{GS} = 20\text{V}$ , $V_{DS} = 0\text{V}$		5	$\mu\text{A}$
			$V_{GS} = -20\text{V}$ , $V_{DS} = 0\text{V}$		-5	$\mu\text{A}$
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		0.4		$\text{V}/^\circ\text{C}$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}$ , $I_D = 1\text{A}$		5.0	6.3	$\Omega$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ISS}$	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$		270	350	pF
Output Capacitance	$C_{OSS}$			38	50	pF
Reverse Transfer Capacitance	$C_{RSS}$			5	7	pF

■ ELECTRICAL CHARACTERISTICS(Cont.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=350V, I_D=2.0A, R_G=25\Omega$ (Note 1, 2)			30	ns
Turn-On Rise Time	$t_R$				80	ns
Turn-Off Delay Time	$t_{D(OFF)}$				50	ns
Turn-Off Fall Time	$t_F$				70	ns
Total Gate Charge	$Q_G$	$V_{DS}=560V, V_{GS}=10V, I_D=2.0A$ (Note 1, 2)		8.1	11	nC
Gate-Source Charge	$Q_{GS}$			1.7		nC
Gate-Drain Charge	$Q_{GD}$			4.4		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0 V, I_{SD} = 2.0 A$			1.4	V
Continuous Drain-Source Current	$I_{SD}$				2.0	A
Pulsed Drain-Source Current	$I_{SM}$				8.0	A
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0 V, I_{SD} = 2.0A$ $di/dt = 100 A/\mu s$ (Note1)		260		ns
Reverse Recovery Charge	$Q_{RR}$			1.09		$\mu C$

Notes: 1. Pulse Test: Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

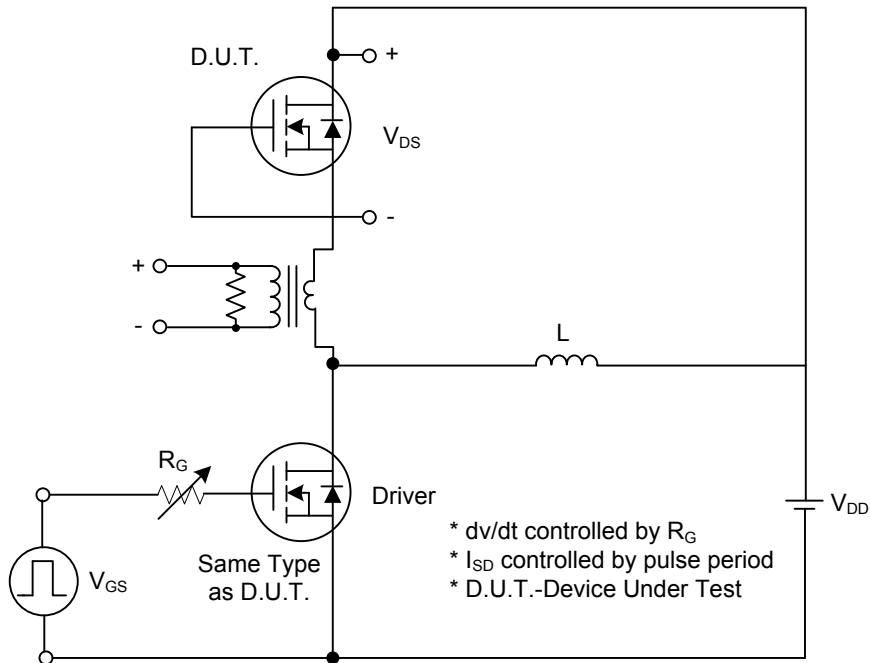


Fig. 1A Peak Diode Recovery dv/dt Test Circuit

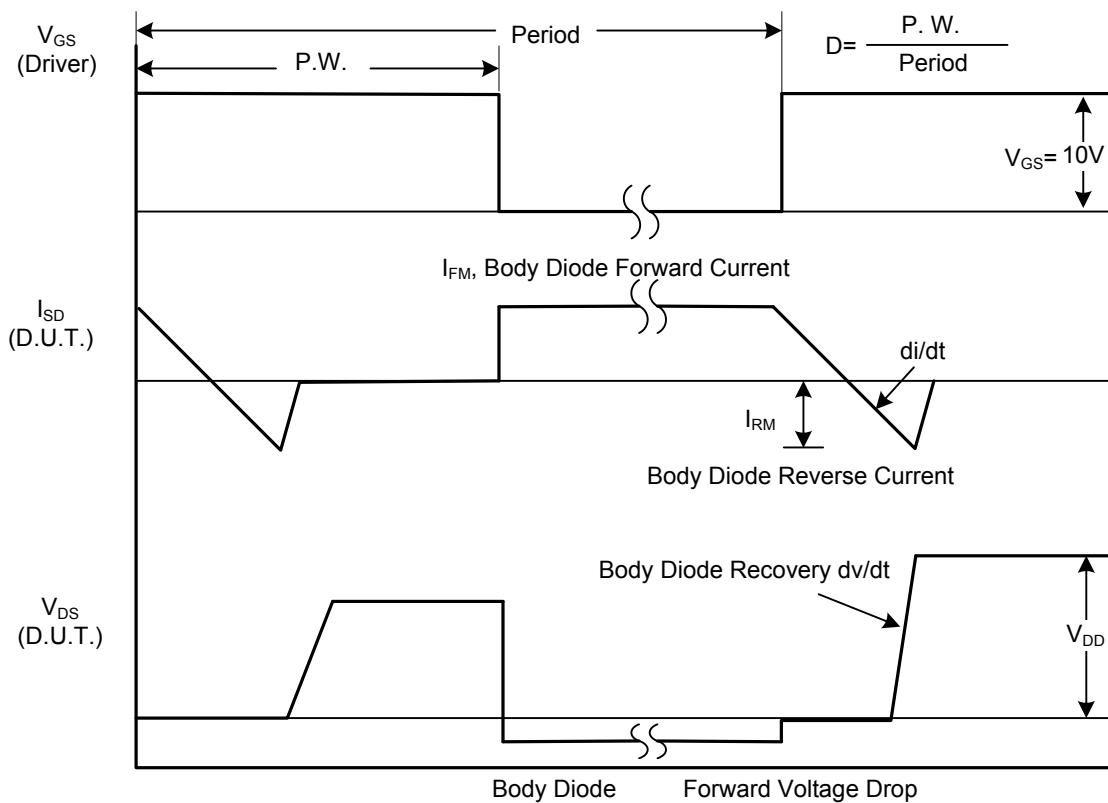


Fig. 1B Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)

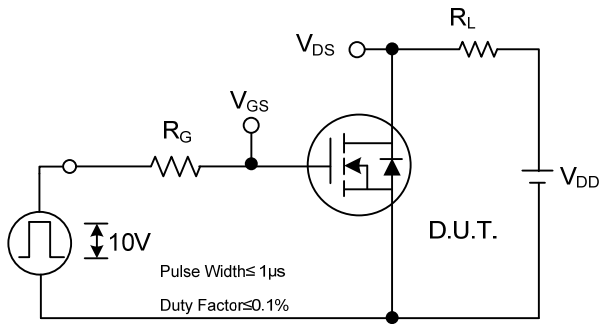


Fig. 2A Switching Test Circuit

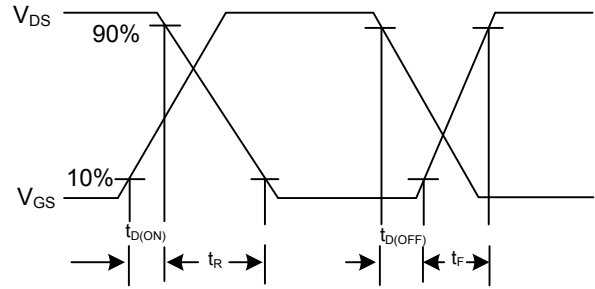


Fig. 2B Switching Waveforms

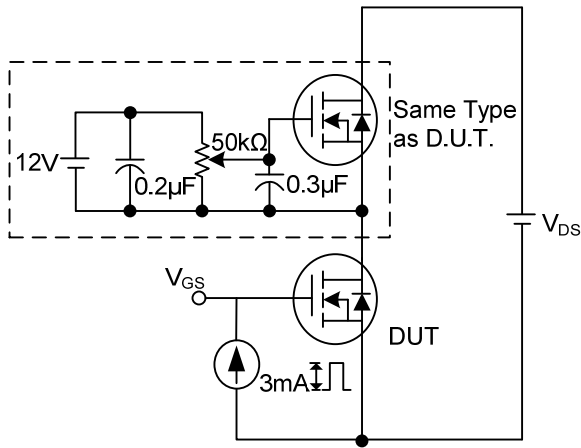


Fig. 3A Gate Charge Test Circuit

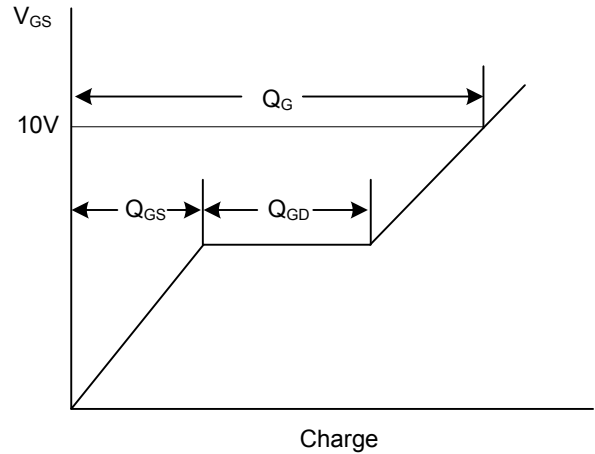


Fig. 3B Gate Charge Waveform

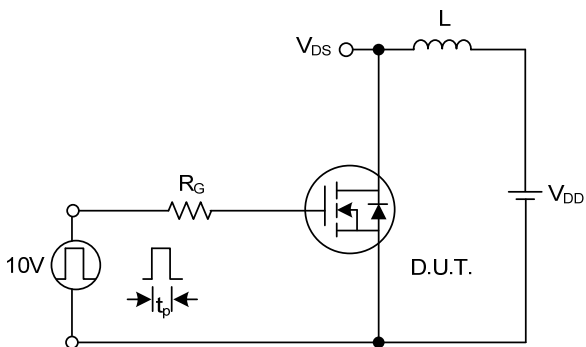


Fig. 4A Unclamped Inductive Switching Test Circuit

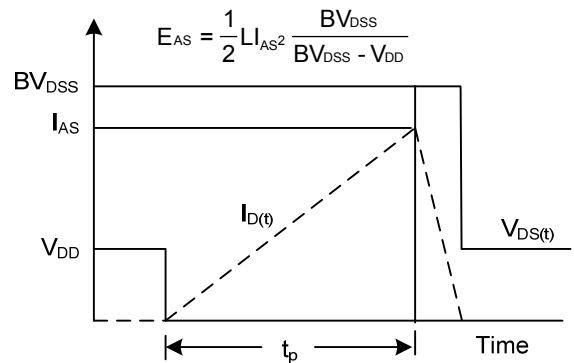
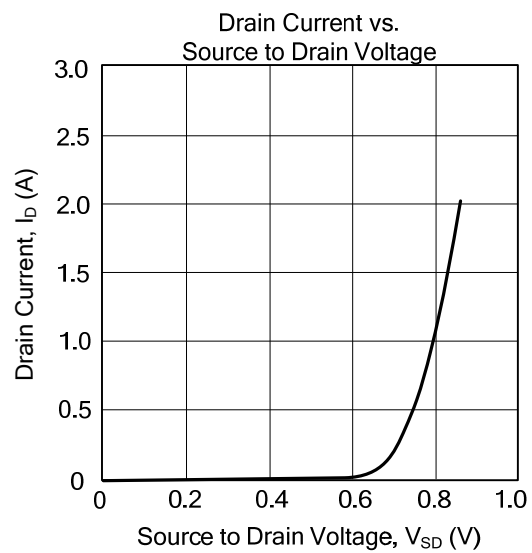
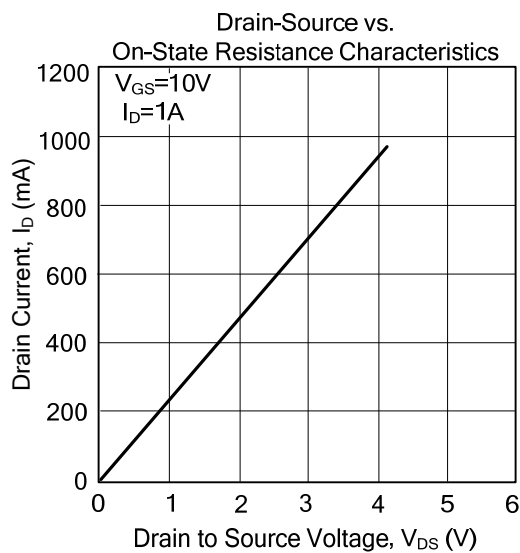
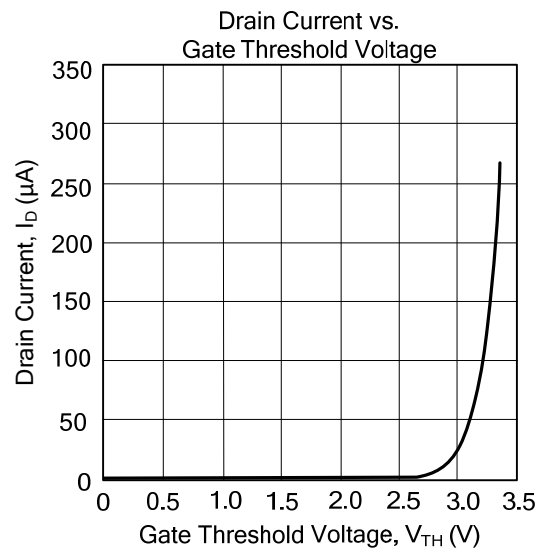
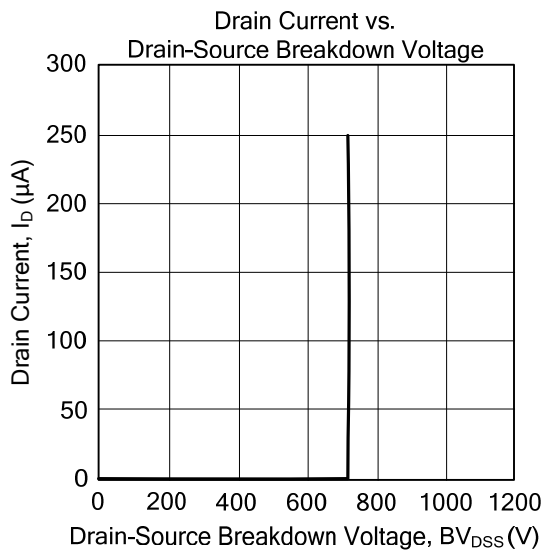


Fig. 4B Unclamped Inductive Switching Waveforms

### TYPICAL CHARACTERISTICS



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